



《风光欣》技术资料

A1586

PNP EPITAXIAL SILICON TRANSISTOR

GENERAL PURPOSE TRANSISTOR

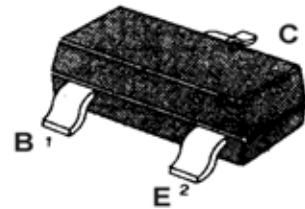
Collector-Emitter Voltage : $V_{CEO} = -50V$

Collector Dissipation: $P_c(\max) = -150mW$

ABSOLUTE MAXIMUM RATINGS($T_A = 25$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter -Base Voltage	V_{EBO}	-5	V
Collector Current	I_c	-150	mA
Collector Dissipation	P_c	100	mW
Junction Temperature	T_j	125	
Storage Temperature	T_{STG}	-55 ~150	

SOT-23



ELECTRICAL CHARACTERISTICS ($T_A = 25$)

Characteristic	Symbol	Test Conditions	Min	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_c = -10 \mu A, I_E = 0$	-40		V
*Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_c = -1mA, I_B = 0$	-40		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = -10 \mu A, I_c = 0$	-6		V
Collector Cut-off Current	I_{CBO}	$V_{CE} = -50V, I_E = 0$		-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_c = 0$		-0.1	μA
*DC Current Gain	H_{FE}	$V_{CE} = -6V, I_c = -2mA$	70	400	
*Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c = -10mA, I_B = -1mA$		-0.25	V
		$I_c = -50mA, I_B = -5mA$		-0.4	V
*Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_c = -10mA, I_B = -1mA$	-0.65	-0.85	V
		$I_c = -50mA, I_B = -5mA$		-0.95	V
Output Capacitance	C_{OB}	$V_{CB} = -5V, I_E = 0, f = 100MHz$		4.5	pF
Current Gain-Bandwidth Product	f_T	$V_{CE} = -10V, I_c = -1mA, f = 100MHz$	80		MHz
Turn On Time	t_{ON}	$V_{CC} = -3V, V_{BE} = -0.5V$		70	ns
		$I_c = -10mA, I_{B1} = -1mA$			
Turn Off Time	t_{OFF}	$V_{CC} = -3V, I_c = -10mA$			
		$I_{B1} = I_{B2} = 1mA$		300	ns